

SANYO	No.3140A	2SC4521
	NPN Epitaxial Planar Silicon Transistor	
High-Speed Switching Applications		

Features

- Adoption of FBET, MBIT processes
- Large current capacity
- Low collector-to-emitter saturation voltage
- Fast switching speed
- Small-sized package

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V _{CB0}	60	V
Collector to Emitter Voltage	V _{CEO}	45	V
Emitter to Base Voltage	V _{EBO}	5	V
Collector Current	I _C	3	A
Collector Current(Pulse)	I _{CP}	6	A
Collector Dissipation	P _C	Mounted on ceramic board (250mm ² × 0.8mm) 1.5 W	
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150 °C	

Electrical Characteristics at Ta = 25°C

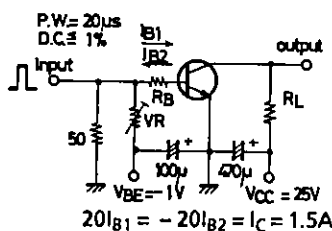
			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 45V, I _E = 0			1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 2V, I _C = 0			10	μA
DC Current Gain	h _{FE} (1)	V _{CE} = 2V, I _C = 500mA	100*		400*	
	h _{FE} (2)	V _{CE} = 2V, I _C = 3A	40			
Gain-Bandwidth Product	f _T	V _{CE} = 2V, I _C = 500mA		300		MHz
Output Capacitance	c _{ob}	V _{CB} = 10V, f = 1MHz		25		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = 1.5A, I _B = 75mA	0.25	0.7		V
B-E Saturation Voltage	V _{BE(sat)}	I _C = 1.5A, I _B = 75mA	0.95	1.3		V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	60			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	45			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = 100μA, I _C = 0	5			V
Turn-ON Time	t _{on}	See specified Test Circuit.		50	100	ns
Storage Time	t _{stg}	//		150	270	ns
Turn-OFF Time	t _{off}	//		180	350	ns

* : The 2SC4521 is classified by 500mA h_{FE} as follows :

100 R 200	140 S 280	200 T 400
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Marking : CL
h_{FE} rank : R,S,T

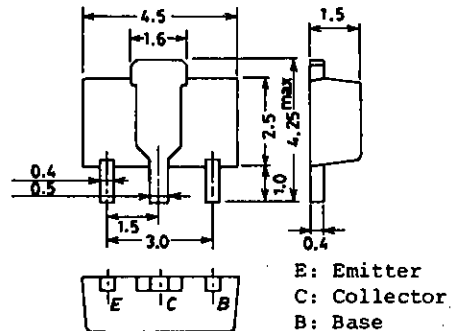
Switching Time Test Circuits



Unit (Resistance : Ω) Unit (Resistance : Ω)

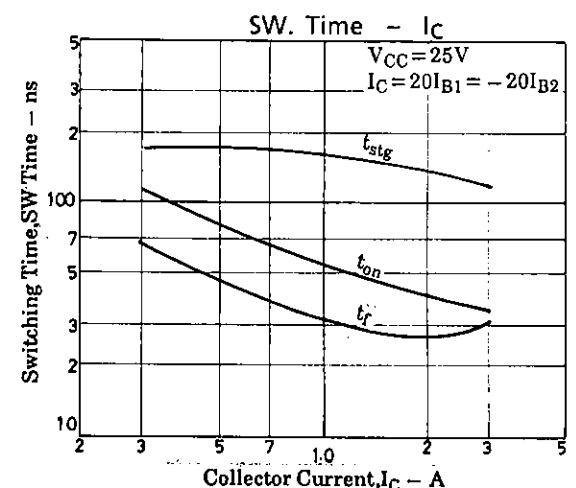
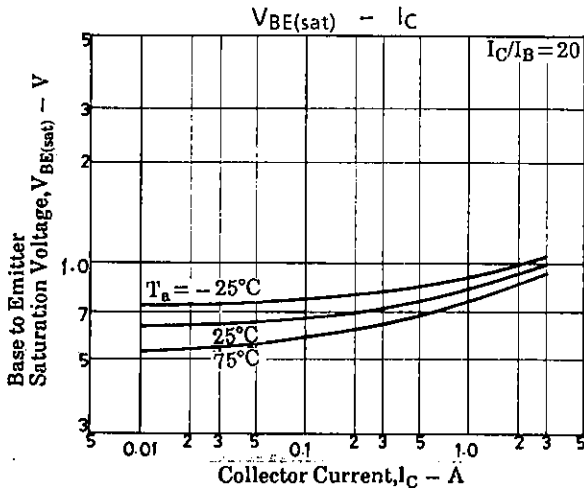
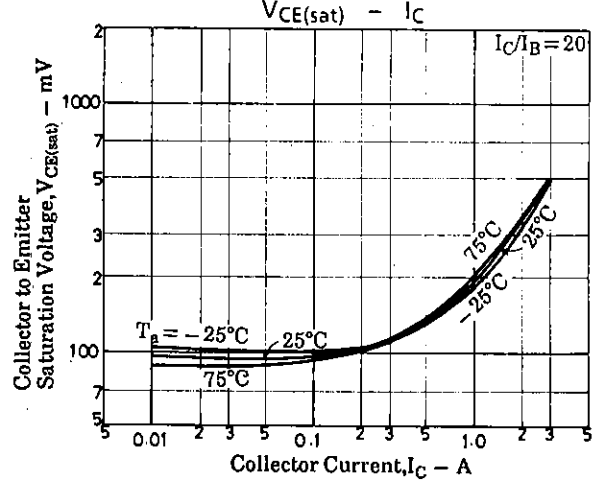
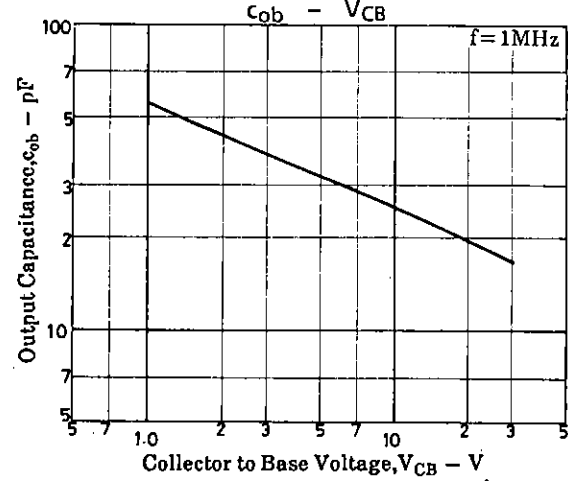
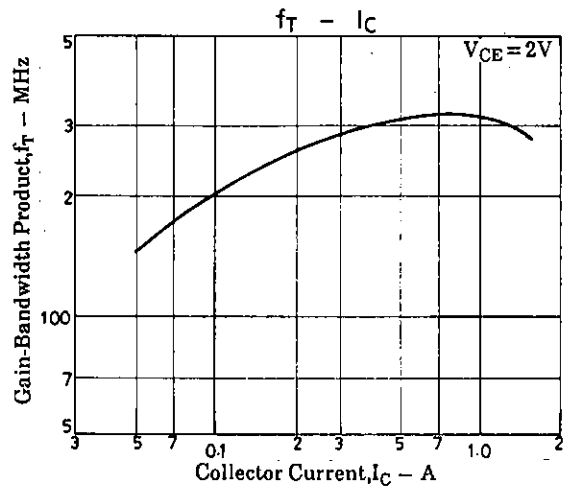
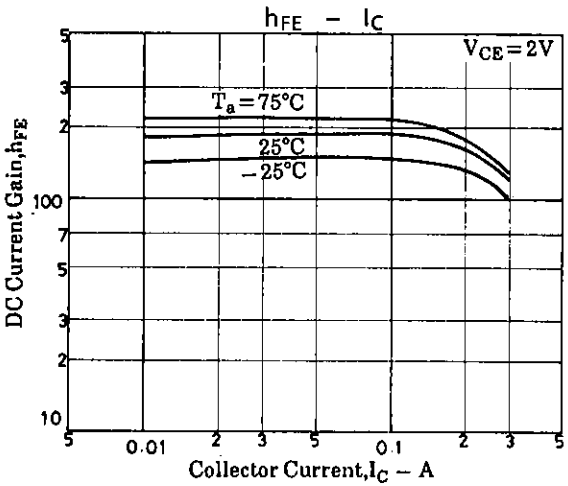
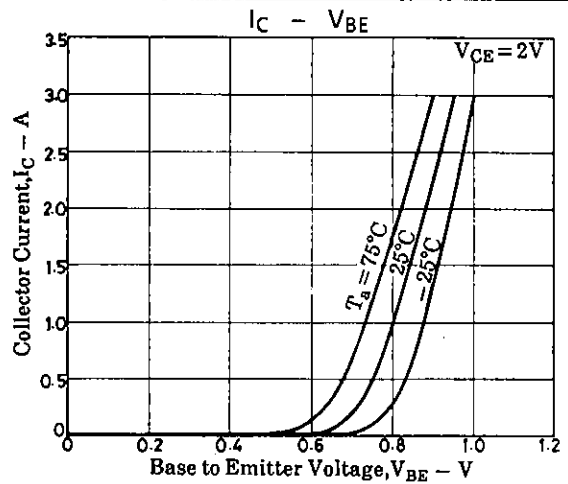
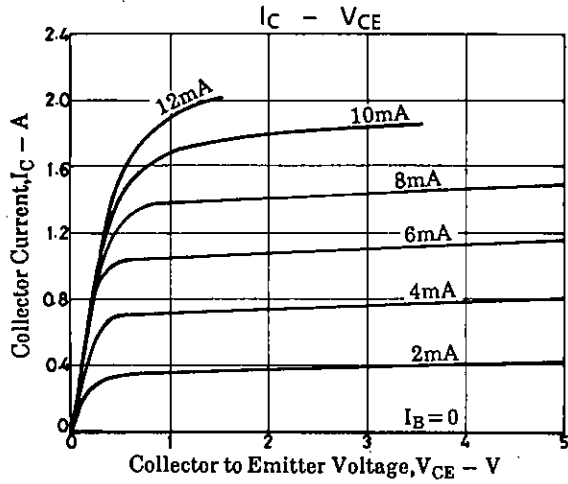
Package Dimensions 2038

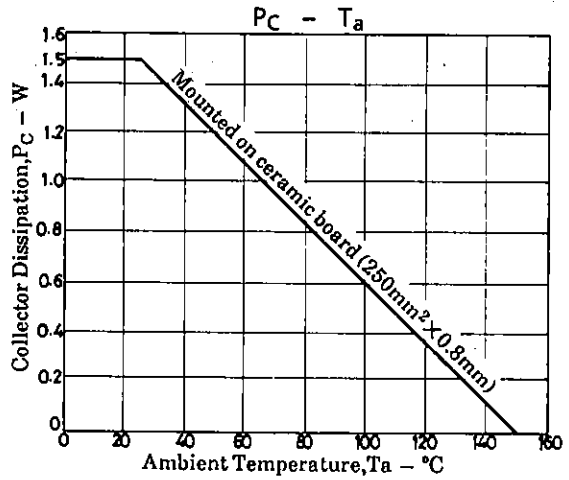
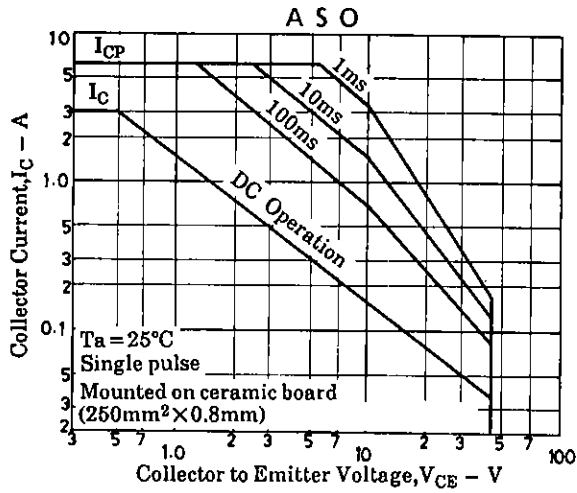
(unit : mm)



E: Emitter
C: Collector
B: Base

SANYO: PCP
(Bottom View)





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